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APR 01 2004  
PATENT & TRADEMARK OFFICE

Atty. Docket No.  
33035M0342

PATENT

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): Kensaku Motoki, et al.

US Serial No.: 10/691,569

Group Art Unit: 2814

Filed: : October 24, 2003

Examiner: To Be Assigned

For : GaN Single Crystal Substrate and Method of Making the Same

**SECOND INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure under 37 C.F.R. 1.56, Applicants are enclosing an Information Disclosure Citation Form (PTO-1449) which lists the references cited in a Supplementary European Search Report issued for corresponding European Appln. No. EP 98 95 0452 dated February 19, 2004. In the Annex to the Search Report, U.S. Patent No. 5,970,314 is identified as a family member of EP 0 801 156. U.S. Patent Nos. 5,962,875 and 5,834,325 are identified as family members of EP 0 810 674. Accordingly, these U.S. patents also are listed on the enclosed PTO-1449 form.

Applicants certify under 37 C.F.R. 1.97(e)(1) that all documents submitted herewith were first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. Therefore, it is respectfully urged that no fees are required for the Examiner's consideration of the documents listed in this Information Disclosure Statement.

It is respectfully requested that the cited documents be considered by the Examiner in the above-identified patent application and that the cited documents be made officially of record therein. It is further requested that a listing of the same appear on the face of any patent which may issue from this application.

Respectfully submitted,  
SMITH, GAMBRELL & RUSSELL, LLP

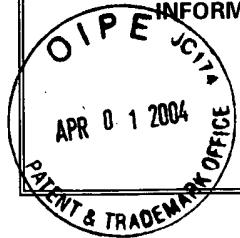
By: 

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Date: April 1, 2004

FORM PTO-1449

## INFORMATION DISCLOSURE STATEMENT

ATTY. DOCKET  
33035M0342  
SERIAL NO.  
10/691,569Applicant  
Kensaku Motoki, et al.FILING DATE  
October 24, 2003  
GROUP ART UNIT  
2814

## U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA	5,970,314	10/19/99	Okahisa, et al.			
	AB	5,962,875	10/5/99	Motoki, et al.			
	AC	5,834,325	11/10/98	Motoki, et al.			

## FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES      NO
	AD	WO 96/41906	12/27/96	PCT			
	AE	EP 0 801 156	10/15/97	EPO			
	AF	EP 0 810 674	12/3/97	EPO			

## OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

	AG	Masaki Nagahara, et al., "Selective Growth of Cubic GaN in Small Areas on Patterned GaAs (100) Substrates by Metalorganic Vapor Phase Epitaxy", Japanese Journal of Applied Physics, Publication Office Japanese Journal of Applied Physics, Vol. 33, No. 1B, Part 1, (1994), pp. 694-697, XP000596419
	AH	X. Li, et al., "Characteristics of GaN Stripes Grown by Selective-Area Metalorganic Chemical Vapor Deposition", Journal of Electronic Materials, Vol. 26, No. 3, (1996), pp. 306-310, XP009004611
	AI	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Matsushima H. et al., "Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO)", Database accession no. 6037425 XP-002268861
	AJ	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Shibata T et al., "Hybrid vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth", Database accession no. 6037423 XP-002268862
	AK	Database Inspec 'Online! Institute of Electrical Engineers, Stevenage, GB; Sasaoka C et al., "High-quality InGaN MQW on low-dislocation-density GaN substrate grown by hydride vapor-phase epitaxy", Database accession no. 6037422 XP-002268863

EXAMINER:

DATE CONSIDERED:

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.